

Abstract of the Disclosure

A semiconductor device includes a semiconductor region of a first conductive type.

5 First and second regions of a second conductive type opposite to the first conductive type are provided in a surface of the semiconductor region in a predetermined interval. A third region of the first conductive type is provided between the first and

10 second regions in the surface of the semiconductor region. A fourth region of the first conductive type is provided below the third region inside the semiconductor region to cover the whole of bottom of the third region at least.